AMENDMENT TO THE CLAIMS

1-30. (Cancelled)

31. (Currently amended) A method for making a device ~~junction~~, comprising the steps of:

irradiating a plasma containing He ~~or a plasma containing Ar~~ to a substrate;

introducing impurities into the substrate; and

irradiating an electromagnetic wave so as to electrically activate the impurities, wherein in the step of irradiating the plasma, an amorphous layer is formed by He-plasma.

32. (Currently amended) A method for making a device ~~junction~~, comprising the steps of:

irradiating ~~either~~ a plasma containing He ~~or a plasma containing Ar~~ and a plasma containing particles to be served as impurities to a substrate, so as to introduce the impurities into the substrate; and

irradiating an electromagnetic wave so as to electrically activate the impurities, wherein in the step of irradiating the plasma, an amorphous layer is formed by He-plasma.

33. (Previously presented) The method for making a junction according to claim 31 or 32, wherein the plasma is primarily comprised of He.

34. (Previously presented) The method for making a junction according to claim 31 or 32, wherein the plasma is comprised of only He.

35. (Canceled)

36. (Previously presented) The method for making a junction according to claim 31 or 32, wherein, assuming that wavelength is λ(nm) and light absorption ratio is A(%), the light absorption rate of a layer which is formed by introducing the impurities into the substrate satisfies at least one of following conditions:

at the wavelength ranging from 375 nm (inclusive) to 500 nm, $A > 7E32\lambda^{-12.316}$;

at the wavelength ranging from 500 nm (inclusive) to 600 nm, $A > 2E19\lambda^{-7.278}$;

at the wavelength ranging from 600 nm (inclusive) to 700 nm, $A > 4E14\lambda^{-5.5849}$; and

at the wavelength ranging from 700 nm (inclusive) to 800 nm, $A > 2E12\lambda^{-4.773}$.

37. (Previously presented) The method for making a junction according to claim 31 or 32, wherein, assuming that wavelength is λ(nm) and absorption coefficient is α (cm^{-1}), the light absorption coefficient of a layer which is formed by introducing the impurities into the substrate satisfies at least one of following conditions:

at the wavelength ranging from 375 nm (inclusive) to 500 nm, $\alpha > 1E38\lambda^{-12.505}$;

at the wavelength ranging from 500 nm (inclusive) to 600 nm, $\alpha > 1E24\lambda^{-7.2684}$;

at the wavelength ranging from 600 nm (inclusive) to 700 nm, $\alpha > 2E19\lambda^{-5.5873}$; and

at the wavelength ranging from 700 nm (inclusive) to 800 nm, $\alpha > 1E17\lambda^{-4.7782}$.

38. (Previously presented) The method for making a junction according to claim 31 or 32, wherein:

the substrate is a silicon substrate; and

the impurities is a boron to be supplied to a surface of the Silicon substrate.

39. (Previously presented) The method for making a junction according to claim 31 or 32, wherein the step of irradiating the electromagnetic wave is a step of irradiating light having an intensity peak at wavelength longer than 375 nm (inclusive).

40. (Previously presented) The method for making a junction according to claim 39, wherein the step of irradiating the electromagnetic wave is a step of irradiating light having an intensity peak at wavelength longer than 375 nm (inclusive) and shorter than 800 nm (inclusive).

41. (Previously presented) The method for making a junction according to claim 40, wherein the light having the intensity peak at the wavelength longer than 375 nm (inclusive) and shorter than 800 nm (inclusive) is a xenon flash lamp light.

42. (Previously presented) The method for making a junction according to claim 38, wherein the silicon substrate is a substrate having a (100) plane or the silicon substrate comprises a plane inclined from the (100) plane by several degrees.

43. (Previously presented) The method for making a junction according to claim 38, wherein, assuming that wavelength is λ(nm) and absorption ratio is A (%), the light absorption ratio of a layer into which the boron is introduced for light having a wavelengths longer than 375 nm (inclusive) and shorter than 800 nm (inclusive) satisfies $A > 1E19\lambda^{-6.833}$.

44. (Previously presented) The method for making a junction according to claim 38, wherein, assuming that wavelength is λ (nm) and absorption coefficient is α (cm^{-1}), the light absorption coefficient of a layer into which the boron is introduced to light having wavelengths longer than 375 nm (inclusive) and shorter than 800 nm (inclusive) satisfies $\alpha > 1E19\lambda^{-7.1693}$.

45. (Previously presented) The method for making a junction according to claim 31 or 32, wherein the step of introducing the impurities is a step of introducing the impurities by plasma doping.

46. (Previously presented) The method for making a junction according to claim 31 or 32, wherein the substrate is a SOI substrate with a Silicon thin film formed on a surface thereof.

47. (Previously presented) The method for making a junction according to claim 31 or 32, wherein the substrate is a strained Si substrate with a Si film formed on a surface thereof.

48. (Previously presented) The method for making a junction according to claim 31 or 32, wherein the substrate is a glass substrate with a poly-Si thin film formed on a surface thereof.

49. (Previously presented) A processed material formed by the method for making a junction according to claim 31 or 32.